

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (L²-π-MOS V)

2SK2883

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS
 CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 3.0\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 2.6S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.)
($V_{DS} = 640V$)
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0V$
($V_{DS} = 10V, I_D = 1mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	800	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)	V_{DGR}	800	V
Gate-Source Voltage	V_{GSS}	± 30	V
Drain Current	DC	I_D	3 A
	Pulse	I_{DP}	9 A
Drain Power Dissipation ($T_c = 25^\circ C$)	P_D	75	W
Single Pulse Avalanche Energy**	E_{AS}	300	mJ
Avalanche Current	I_{AR}	3	A
Repetitive Avalanche Energy*	E_{AR}	7.5	mJ
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	1.67	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	83.3	$^\circ C/W$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 90V$, Starting $T_{ch} = 25^\circ C$, $L = 60.0mH$, $R_G = 25\Omega$, $I_{AR} = 3A$

**This transistor is an electrostatic sensitive device.
 Please handle with caution.**

INDUSTRIAL APPLICATIONS

TO-220FL

Unit in mm

JEDEC	—
EIAJ	—
TOSHIBA	2-10S1B

Weight : 1.5g (Typ.)

TO-220SM

JEDEC	—
EIAJ	—
TOSHIBA	2-10S2B

Weight : 1.5g (Typ.)

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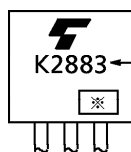
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	—	—	± 10	μA
Gate-Source Breakdown Voltage		$V_{(BR)GSS}$	$I_G = \pm 10\mu A, V_{DS} = 0V$	± 30	—	—	V
Drain Cut-Off Current		I_{DSS}	$V_{DS} = 640V, V_{GS} = 0V$	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = 10mA, V_{GS} = 0V$	800	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS} = 10V, I_D = 1mA$	2.0	—	4.0	V
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1.5A$	—	3.0	3.6	Ω
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 20V, I_D = 1.5A$	0.65	2.6	—	S
Input Capacitance		C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	—	750	—	pF
Reverse Transfer Capacitance		C_{rss}		—	10	—	
Output Capacitance		C_{oss}		—	70	—	
Switching Time	Rise Time	t_r	<p>$I_D = 1.5A$ $V_{GS} = 10V, 0V$ V_{OUT} $R_L = 133\Omega$ $V_{DD} \doteq 200V$ $V_{IN} : t_r, t_f < 5ns,$ $Duty \leq 1\%, t_w = 10\mu s$</p>	—	15	—	ns
	Turn-On Time	t_{on}		—	55	—	
	Fall Time	t_f		—	30	—	
	Turn-Off Time	t_{off}		—	110	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD} \doteq 400V, V_{GS} = 10V,$ $I_D = 3A$	—	25	—	nC
Gate-Source Charge		Q_{gs}		—	13	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	12	—	

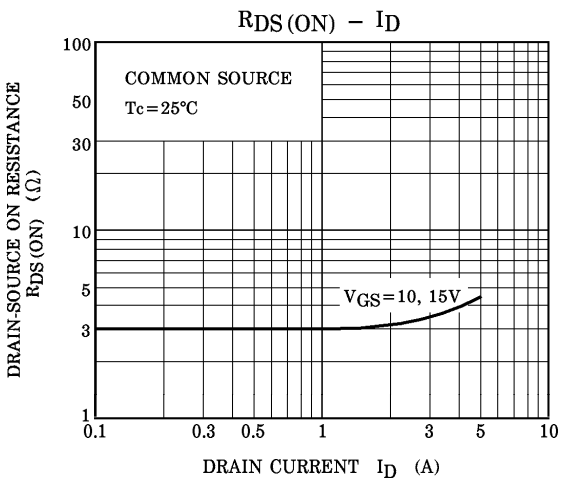
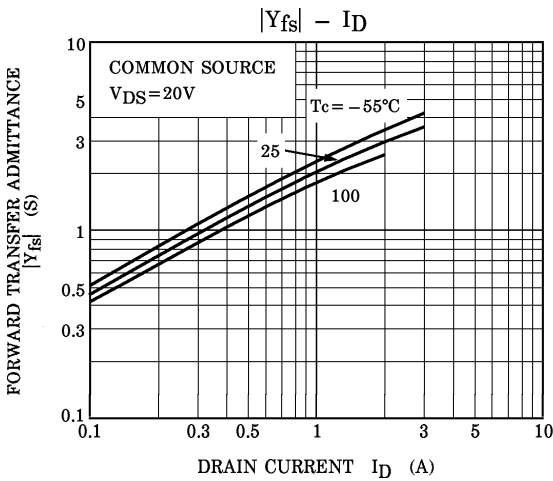
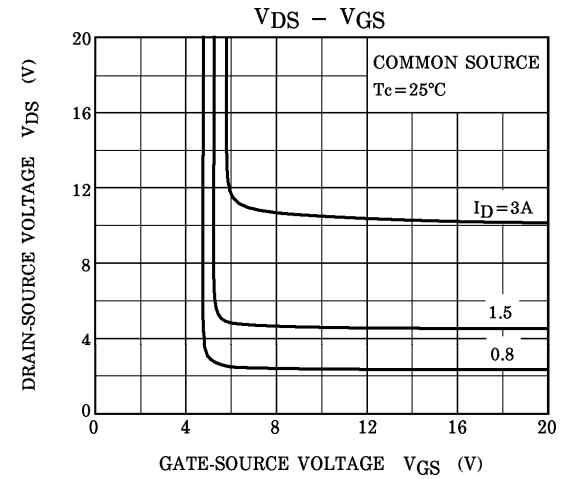
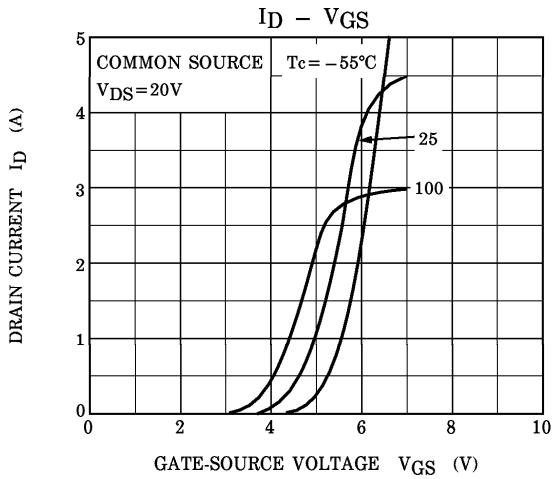
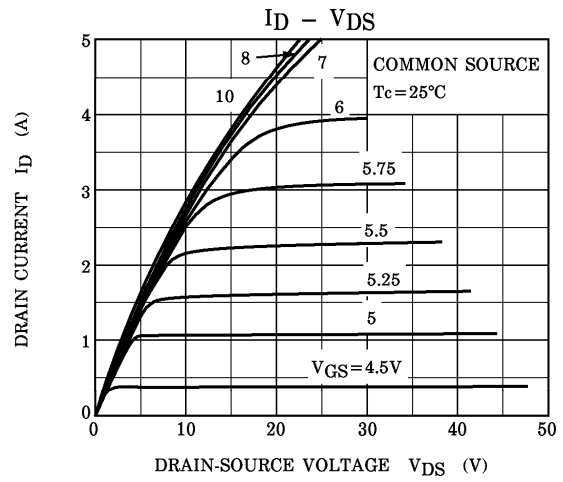
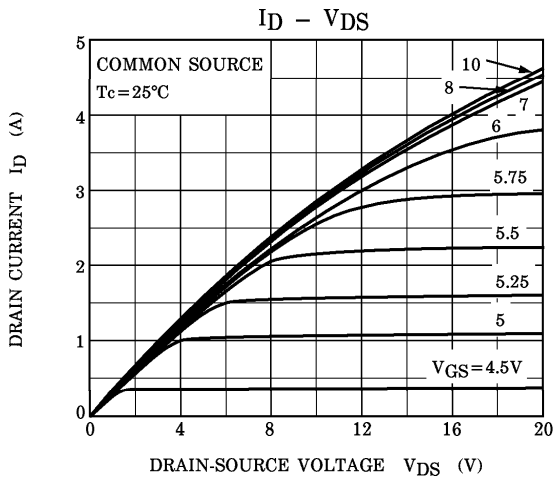
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

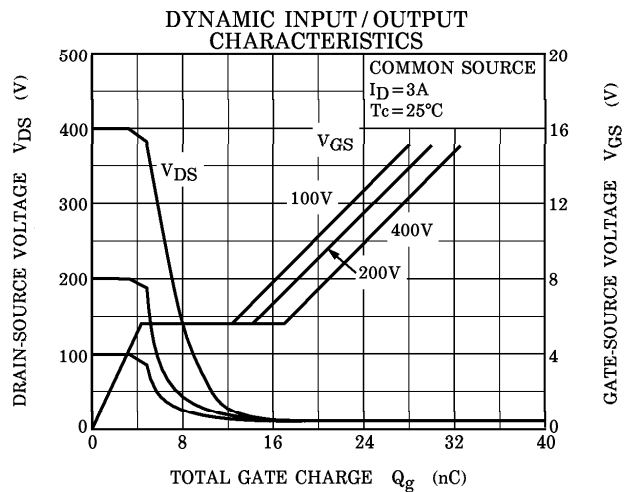
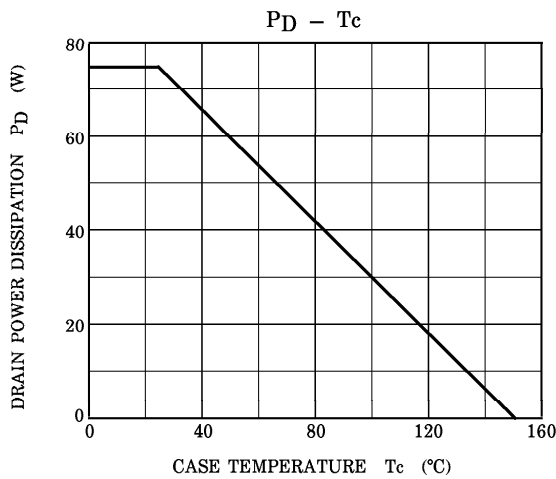
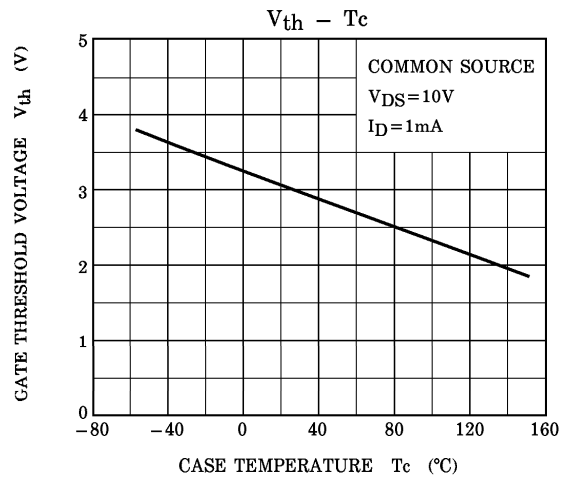
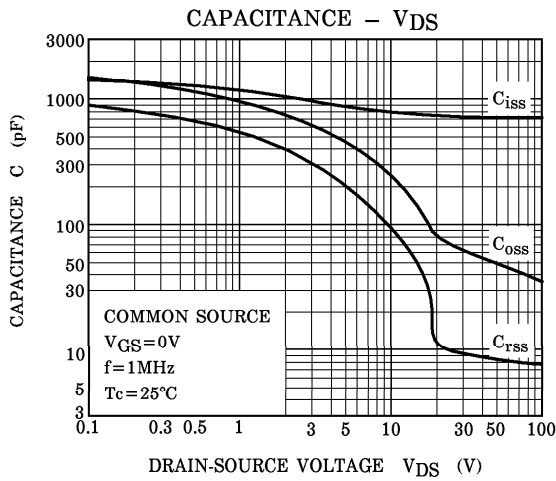
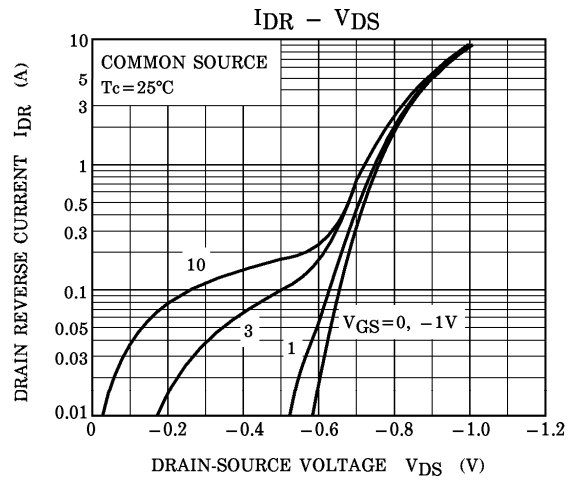
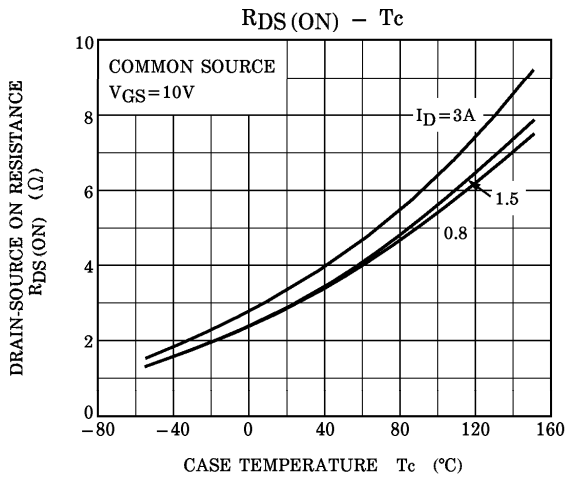
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	3	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	9	A
Diode Forward Voltage	V_{DSF}	$I_{DR} = 3A, V_{GS} = 0V$	—	—	-1.9	V
Reverse Recovery Time	t_{rr}	$I_{DR} = 3A, V_{GS} = 0V$	—	900	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR}/dt = 100A/\mu s$	—	6	—	μC

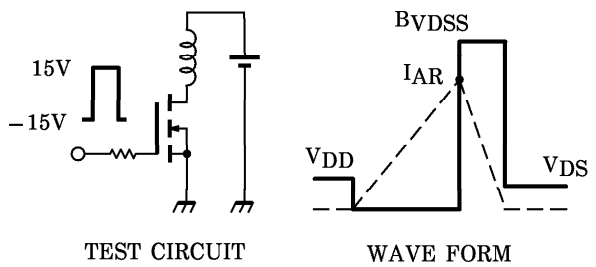
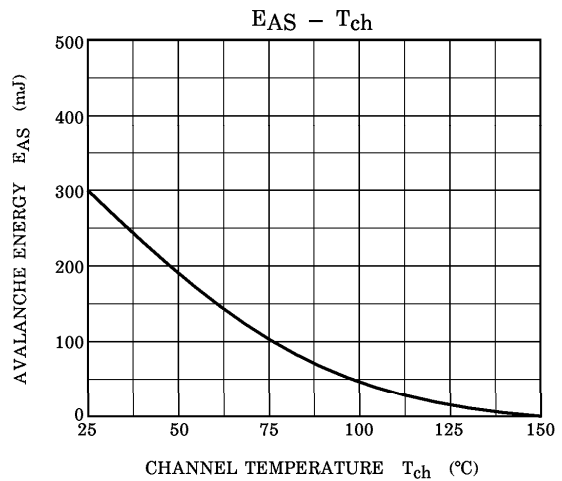
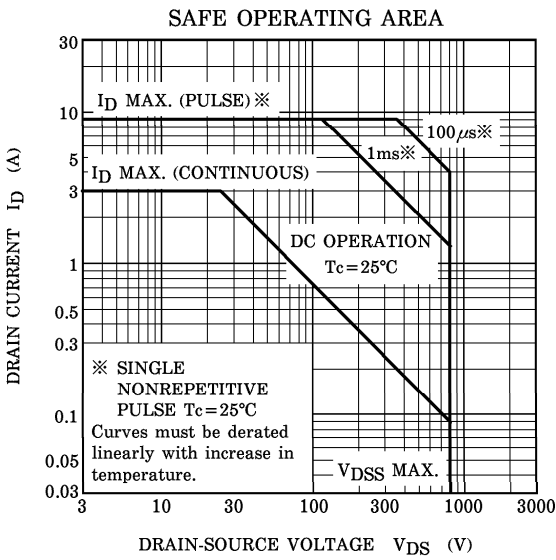
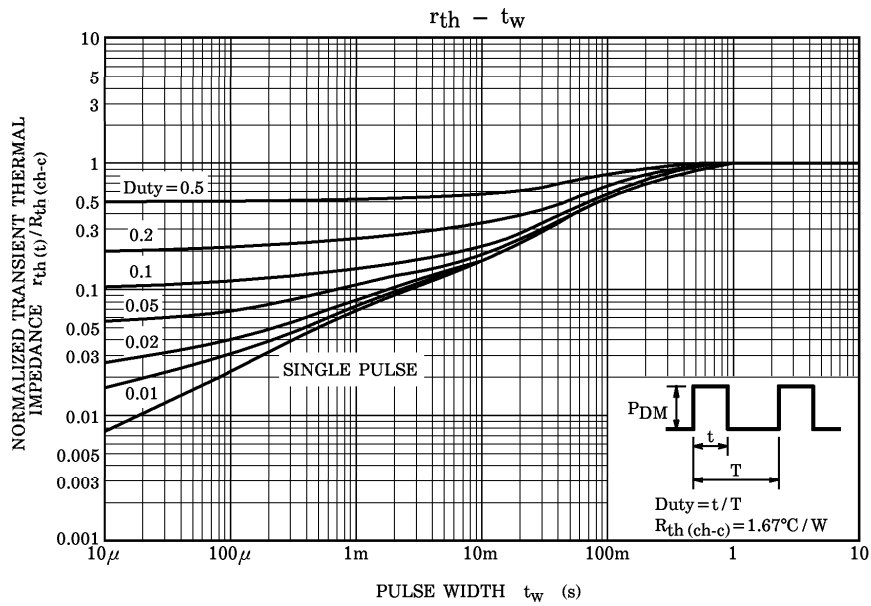
MARKING



← TYPE
※ Lot Number
□ □ — Month (Starting from Alphabet A)
□ — Year (Last Number of the Christian Era)







Peak $I_{AR} = 3A$, $R_G = 25\Omega$
 $V_{DD} = 90V$, $L = 60mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$